FIG. **2**A is a perspective view of an exemplary embodiment of a structure for an integrated circuit having a substrate with an SDB just prior to initiation of epitaxial growth within S/D regions in accordance with the present invention;

FIG. **2**B is a cross sectional view of FIG. **2**A taken along the line **2**B-**2**B;

FIG. **2**C is a cross sectional view of FIG. **2**A taken along the line **2**C-**2**C;

FIG. **3** is a perspective view of the structure of FIG. **1**A prior to formation of fins;

FIG. **4** is a perspective view of the structure of FIG. **3** after fins are patterned into the substrate;

FIG. **5**A is a top view of an exemplary embodiment of the structure of FIG. **4** having a first dielectric fill material disposed thereon;

FIG. **5**B is a cross sectional view of FIG. **5**A taken along the line **5**B-**5**B;

FIG. **5**C is a cross sectional view of FIG. **5**A taken along the line **5**C-**5**C;

FIG. **5**D is a cross sectional view of FIG. **5**A taken along the line **5**D-**5**D;

FIG. **6**A is a top view of an exemplary embodiment of the structure of FIG. **5**A having a photo resist layer disposed over the entirety of the first dielectric fill material;

FIG. **6**B is a cross sectional view of FIG. **6**A taken along the line **6**B-**6**B;

FIG. **6**C is a cross sectional view of FIG. **6**A taken along the line **6**C-**6**C;

FIG. **6**D is a cross sectional view of FIG. **6**A taken along the line **6**D-**6**D;

FIG. **7**A is a top view of an exemplary embodiment of the structure of FIG. **6**A after an isolation region has been anisotropically etched into the structure;

FIG. **7**B is a cross sectional view of FIG. **7**A taken along the line **7**B-**7**B;

FIG. **7**C is a cross sectional view of FIG. **7**A taken along the line **7**C-**7**C;

FIG. **7**D is a cross sectional view of FIG. **7**A taken along the line **7**D-**7**D;

FIG. **8**A is a top view of an exemplary embodiment of the structure of FIG. **7**A after self-aligned resist edges of a resist strip have been trimmed;

FIG. **8**B is a cross sectional view of FIG. **8**A taken along the line **8**B-**8**B;

FIG. **8**C is a cross sectional view of FIG. **8**A taken along the line **8**C-**8**C;

FIG. **8**D is a cross sectional view of FIG. **8**A taken along the line **8**D-**8**D;

FIG. **9**A is a top view of an exemplary embodiment of the structure of FIG. **8**A after exposed end portions of a fin hardmask have been removed;

FIG. **9**B is a cross sectional view of FIG. **9**A taken along the line **9**B-**9**B;

FIG. **9**C is a cross sectional view of FIG. **9**A taken along the line **9**C-**9**C;

FIG. **9**D is a cross sectional view of FIG. **9**A taken along the line **9**D-**9**D;

FIG. **10**A is a top view of an exemplary embodiment of the structure of FIG. **9**A after a remaining photoresist layer has been removed;

FIG. **10**B is a cross sectional view of FIG. **10**A taken along the line **10**B-**10**B;

FIG. **10**C is a cross sectional view of FIG. **10**A taken along the line **10**C-**10**C;

FIG. **10**D is a cross sectional view of FIG. **10**A taken along the line **10**D-**10**D;

FIG. **11**A is a top view of an exemplary embodiment of the structure of FIG. **10**A after a second dielectric fill material has been dispose over the structure;

FIG. **11**B is a cross sectional view of FIG. **11**A taken along the line **11**B-**11**B;

FIG. **11**C is a cross sectional view of FIG. **11**A taken along the line **11**C-**11**C;

FIG. **11**D is a cross sectional view of FIG. **11**A taken along the line **11**D-**11**D;

FIG. **12**A is a top view of an exemplary embodiment of the structure of FIG. **11**A after the first dielectric fill material has been recessed;

FIG. **12**B is a cross sectional view of FIG. **10**A taken along the line **12**B-**12**B;

FIG. **12**C is a cross sectional view of FIG. **12**A taken along the line **12**C-**12**C;

FIG. **12**D is a cross sectional view of FIG. **12**A taken along the line **12**D-**12**D;

FIG. **13**A is a top view of an exemplary embodiment of the structure of FIG. **12**A after the remaining fin hardmask has been removed;

FIG. **13**B is a cross sectional view of FIG. **13**A taken along the line **13**B-**13**B;

FIG. **13**C is a cross sectional view of FIG. **13**A taken along the line **13**C-**13**C;

FIG. **13**D is a cross sectional view of FIG. **13**A taken along the line **13**D-**13**D;

FIG. **14**A is a top view of an exemplary embodiment of the structure of FIG. **13**A after a dummy gate and active gates have been disposed thereon;

FIG. **14**B is a cross sectional view of FIG. **14**A taken along the line **14**B-**14**B;

FIG. **14**C is a cross sectional view of FIG. **14**A taken along the line **14**C-**14**C; and

FIG. **14**D is a cross sectional view of FIG. **14**A taken along the line **14**D-**14**D.

DETAILED DESCRIPTION

Certain exemplary embodiments will now be described to provide an overall understanding of the principles of the structure, function, manufacture, and use of the methods, systems, and devices disclosed herein. One or more examples of these embodiments are illustrated in the accompanying drawings. Those skilled in the art will understand that the methods, systems, and devices specifically described herein and illustrated in the accompanying drawings are non-limiting exemplary embodiments and that the scope of the present invention is defined solely by the claims. The features illustrated or described in connection with one exemplary embodiment may be combined with the features of other embodiments. Such modifications and variations are intended to be included within the scope of the present invention.

Referring to FIGS. **1**A, **1**B and **1**C, an exemplary embodiment of a structure **10** for an integrated circuit formed utilizing FinFET technology and having a prior art single diffusion break (SDB) **12** is presented. FIG. **1**A is a perspective view of structure **10** at an intermediate stage of its manufacturing process, just prior to initiation of epitaxial growth within source/drain (S/D) regions **14** and **16**. FIG. **1**B is a cross sectional view of FIG. **1**A taken along the line **1**B-**1**B, which cuts through fins **26** and **36**. FIG. **1**C is a cross sectional view of FIG. **1**A taken along the line **1**C-**1**C, which cuts a region between the parallel rows of fins.

Structure **10** includes a pair of opposing active Rx regions **18** and **20**, which are separated by an isolation region **22**. In